Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (L^2 - π -MOSV)

2SK2782

Chopper Regulator, DC-DC Converter and Motor Drive Applications

• 4 V gate drive

• Low drain–source ON resistance : R_{DS} (ON) = 0.039 Ω (typ.)

• High forward transfer admittance $: |Y_{fs}| = 11 \text{ S (typ.)}$ • Low leakage current $: I_{DSS} = 100 \,\mu\text{A (max) (V}_{DS} = 60 \,\text{V)}$

• Enhancement-mode : $V_{th} = 0.8 \sim 2.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA)}$

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	60	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V_{DGR}	60	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	20	Α	
	Pulse (Note 1)	I _{DP}	50	Α	
Drain power dissipation (Tc = 25°C)		P_{D}	40	W	
Single pulse avalanche energy (Note 2)		E _{AS}	156	mJ	
Avalanche current		I _{AR}	20	Α	
Repetitive avalanche energy (Note 3)		E _{AR}	4	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	3.125	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	125	°C/W

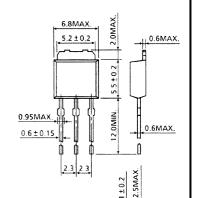
Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2: V_{DD} = 25 V, T_{ch} = 25°C (initial), L = 530 μ H, R_G = 25 Ω , I_D = 20 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.

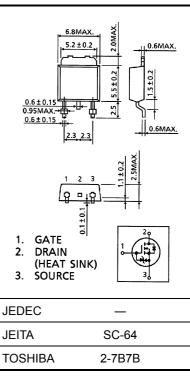
Please handle with caution.



1. GATE
2. DRAIN
(HEAT SINK)
3. SOURCE

JEDEC —
JEITA SC-64
TOSHIBA 2-7B5B

Weight: 0.36 g (typ.)



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TOSHIBA

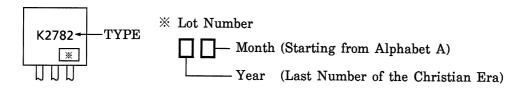
Electrical Characteristics (Ta = 25°C)

Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cu	ırrent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	_	_	±10	μΑ	
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	-	_	100	μA	
Drain-source br	eakdown voltage	V _{(BR) DSS}	I _D = 10 mA, V _{GS} = 0 V	60	_	_	V	
Gate threshold v	oltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	0.8	_	2.0	٧	
Drain-source ON resistance		R _{DS (ON)}	V _{DS} = 4 V, I _D = 5 A	_	0.06	0.09	Ω	
			V _{DS} = 10 V, I _D = 10 A	1	0.039	0.055		
Forward transfer	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 10 A	7	11	_	S	
Input capacitano	e	C _{iss}		_	880	_		
Reverse transfer capacitance		C _{rss}	C_{rss} $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ C_{oss}	_	90	_	pF	
Output capacitance		Coss		_	330	_		
Switching time	Rise time	t _r	V_{GS} $0V$ $I_{D}=10A$ $R_{L}=3.0\Omega$ $V_{DD}=30V$	_	15	_		
	Turn-on time	t _{on}		_	25	_	ne	
	Fall time	t _f		1	30	_	- ns	
	Turn-off time	t _{off}	Duty $\leq 1\%$, $t_{\mathbf{W}} = 10 \mu \text{s}$		100	_		
Total gate charge (gate-source plus gate-drain)		Qg	V _{DD} ≈ 48 V, V _{GS} = 10 V, I _D = 20 A		25		nC	
Gate-source charge		Q _{gs}			19	_		
Gate-drain ("miller") Charge		Q_{gd}			6	_		

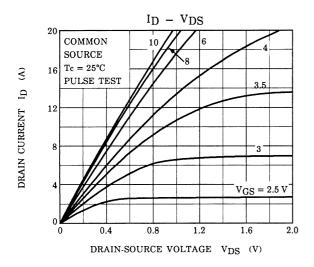
Source-Drain Ratings and Characteristics (Ta = 25°C)

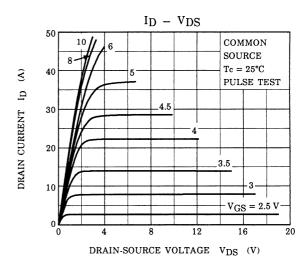
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	20	Α
Pulse drain reverse current (Note 1)	I _{DRP}	-	_	_	50	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 20 A, V _{GS} = 0 V	_	_	-2.0	V
Reverse recovery time	t _{rr}	I _{DR} = 20 A, V _{GS} = 0 V, dI _{DR} / dt = 50 A / μs	_	60		ns
Reverse recovery charge	Q _{rr}	1DR - 20 Λ, VGS - 0 V, αιDR / αι - 30 Λ / μS		45	_	μC

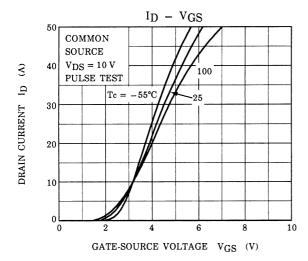
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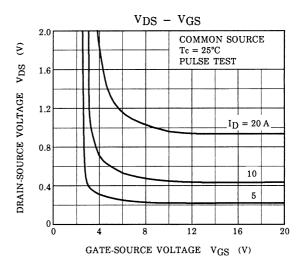


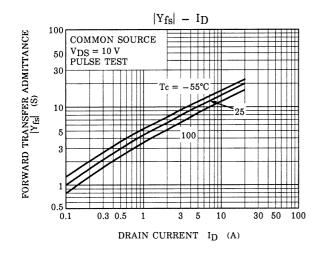
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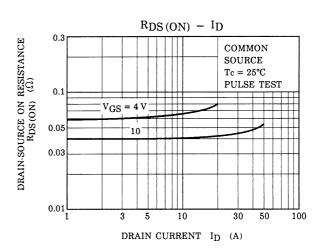




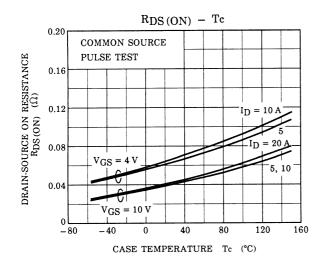


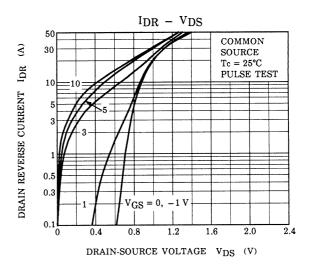


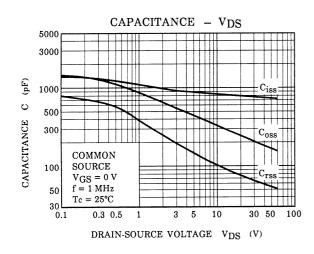


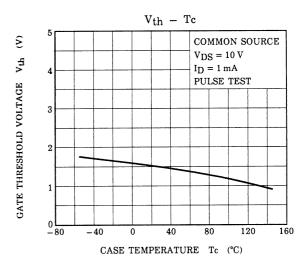


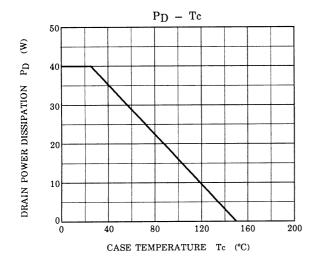
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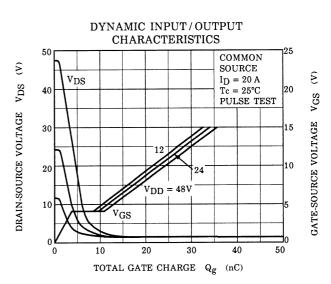




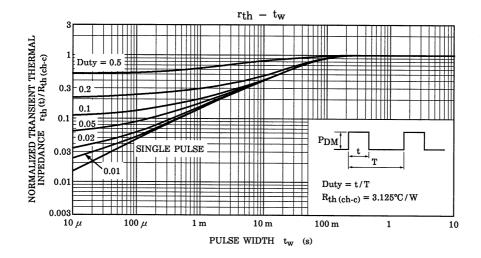


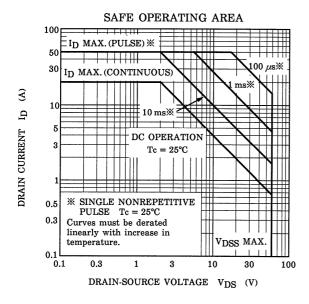


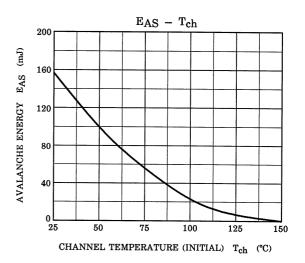


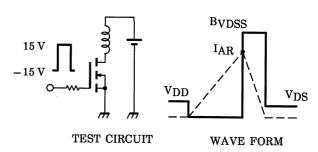


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$$R_G$$
 = 25 Ω
 V_{DD} = 25 V, L = 530 μH

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$$EAS = \frac{1}{2} \cdot L \cdot I^{2} \cdot \left(\frac{BVDSS}{BVDSS - VDD} \right)$$

RESTRICTIONS ON PRODUCT USE

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